

PRELIMINARY
 Notice : This is not a final specification
 Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs MMIC>

MGFC5212

K-Band 2-Stage Power Amplifier

Target Specifications

ELECTRICAL CHARACTERISTICS (Ta=25 Degree C.)

Symbol	Parameter	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS1	Drain Saturation Current	Vd=3.0V	150.0		240.0	mA
IDSS2	Drain Saturation Current		300.0		480.0	mA
Vp1	Pinch Off Voltage	Vd=3.0V,Id=0.6mA	-2.0		-1.0	V
Vp2	Pinch Off Voltage	Vd=3.0V,Id=1.2mA	-2.0		-1.0	V
P1dB	Output Power at 1 dB Compression Point	f=24.5-26.5 GHz, Vd1=Vd2=6.0V , Id1=90mA* , Id2=180mA*	23.0			dBm
Gain	Gain		13.0			dB
Inpur Return Loss	Inpur Return Loss			10.0		dB
Out Put Return Loss	Out Put Return Loss			10.0		dB
IM3	Inter Modulation Level	f=24.5-26.5 GHz, Vd1=Vd2=6.0V , Id1=90mA* ,Id2=180 mA* , Pout=20dBm	22.0			dBc

*:Ids at RF off